

Surface Mount Glass Passivated Standard Rectifier

			Feat	ures							
DO-213AA			 ROHS compliant Glass passivated chip High forward surge capability Meet MSL level 1, per J-STD-020 LF maximum peak of 250 °C Solder dip 260 °C / 40S Component in accordance to ROHS 2002/95/EC and WEEE 2002/96/WC UL recognition, file number E342874 								
Primary characteristics			App	licatio	ons						
I _{F(AV)}		1A	Ideal	for ac-	-to-dc	bridge	e full w	vave re	ectifica	ation s	uck as
V _{RRM}	50V t	o 1000V	SMP	S, hom	ne app	lianes	, office	e equi	pmen	t, indus	srial
I _{FSM}		25A	auton	automation applicatios							
I _{RM}	Į	5uA	1								
V _{FM} at I _F =1A	1	.1V	Mechanical data								
T _J max.	15	50 °C	• DO-213AA								
Maximum rating (Ta:	=25°C เ	unless othe	• Mo • Re	comm	g Torqu iendec	ue:10c I Torqi	ue:5.7	cm-k		bs)ma ches-lb	
Parameter			Sym	DO - 213AA GL1A GL1B GL1D GL1G GL1J GL1K GL1M		CI 1M	Unit				
Max. repetitive peak reverse	voltage							-		GLIN	Unit
	vonago		Vrrm	50	100	200	400	600	800	1000	V
Max. RMS reverse voltage	voltago		V _{RRM} V _{RMS}	50 35	100 70	200 140	400 280	600 420	800 560	-	
Max. RMS reverse voltage Max. DC blocking voltage	voltage									1000	V
Max. DC blocking voltage Max. average forward curren	it		Vrms	35	70	140	280	420	560	1000 700	V
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward	it	rent	V _{RMS} V _{DC}	35	70	140	280 400 1	420	560	1000 700	V V V
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward 8.3ms single half-sine-wave	nt surge cur		Vrms Vdc If(av) Ifsm	35	70	140 200	280 400 1 25	420 600	560	1000 700	V V V A A
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward	it surge curi voltage di	op per diode	VRMS VDC IF(AV)	35	70	140 200	280 400 1 25 .1 (1A)	420 600	560	1000 700	V V V A A V
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse	it surge curr voltage di current	op per diode Ta=25 °C	Vrms Vdc If(av) Ifsm	35	70	140 200	280 400 1 25 .1 (1A) 5	420 600	560	1000 700	V V Α Α V μΑ
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage	it surge curi voltage di current	op per diode	V _{RMS} V _{DC} I _{F(AV)} I _{FSM} V _{FM}	35	70	140 200 1	280 400 1 25 .1 (1A) 5 50	420 600	560	1000 700	V V V A A V
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperatu	it surge curi voltage di current	op per diode Ta=25 °C	VRMS VDC IF(AV) IFSM VFM	35	70	140 200 1 -5:	280 400 1 25 .1 (1A) 5	420 600	560	1000 700	V V V A A V μA μA
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward s 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperatu	nt surge curr voltage dr current ure	op per diode Ta=25 °C Ta=125 °C	V _{RMS} V _{DC} I _{F(AV)} I _{FSM} V _{FM} I _{RM} T _J	35	70	140 200 1 -5:	280 400 1 25 .1 (1A) 5 50 5 ~ +15	420 600	560	1000 700	V V A A V μA °C
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperatu	nt surge curr voltage dr current ure	op per diode Ta=25 °C Ta=125 °C	VRMS VDC IF(AV) IFSM VFM IRM TJ TSTG	35	70	140 200 1 -5:	280 400 1 25 .1 (1A) 5 50 5 ~ +15 5 ~ +15	420 600	560	1000 700	V V V A A V μA ωC ωC
Max. DC blocking voltage Max. average forward curren Non-repetitive peak forward s 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperatu	it surge curr voltage dr current ure	op per diode Ta=25 °C Ta=125 °C	VRMS VDC IF(AV) IFSM VFM IRM TJ TSTG R J-A	35	70	140 200 1 -5:	280 400 1 25 .1 (1A) 5 50 5 ~ +15 5 ~ +15 75	420 600	560	1000 700	V V V A A V μA °C °C °C/W

Notes: 1 Thermal resistance from junction to ambient, 0.24×0.24(6.0×6.0mm) copper pads to each terminal

2 Thermal resistance from junction to terminal,0.24×0.24(6.0×6.0mm)copper pads to each terminal

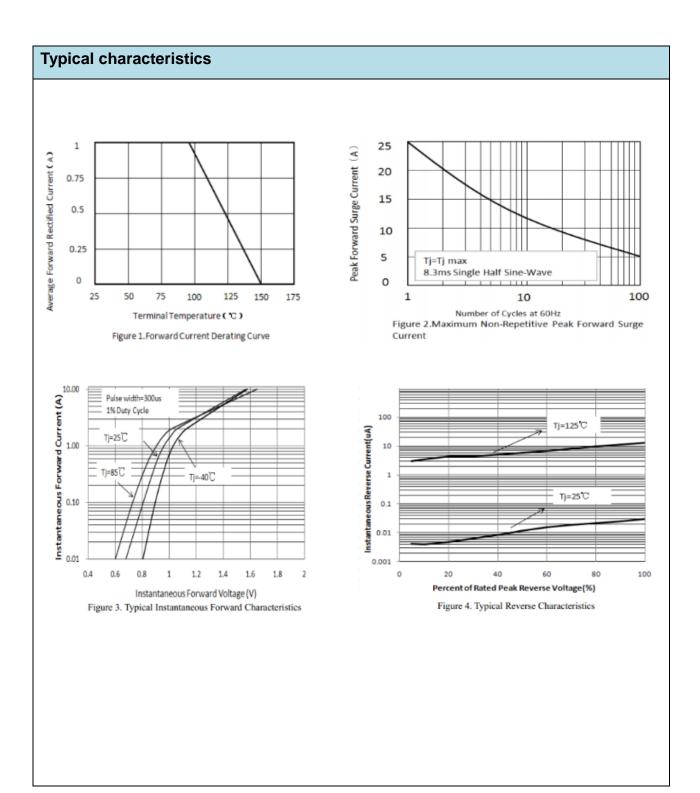
3 Measured at 1 MHz and Applied Reverse Voltage of 4.0 V D.C

4 Reverse recovery test conditions: IF=0.5A, IR=1.0A, Irr=0.25A



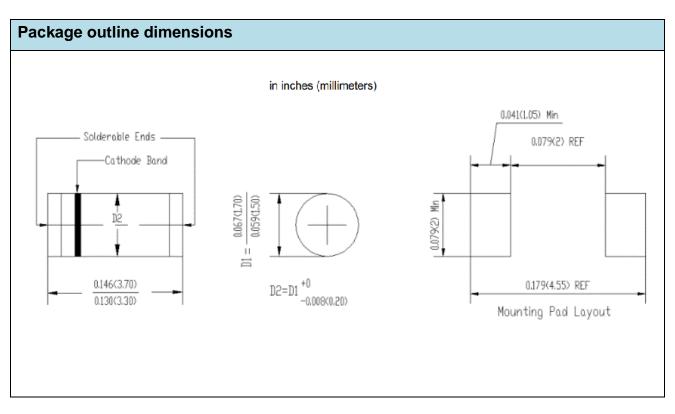
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Ordering information (Example)								
PREFERRED	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE				
GL1M								





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